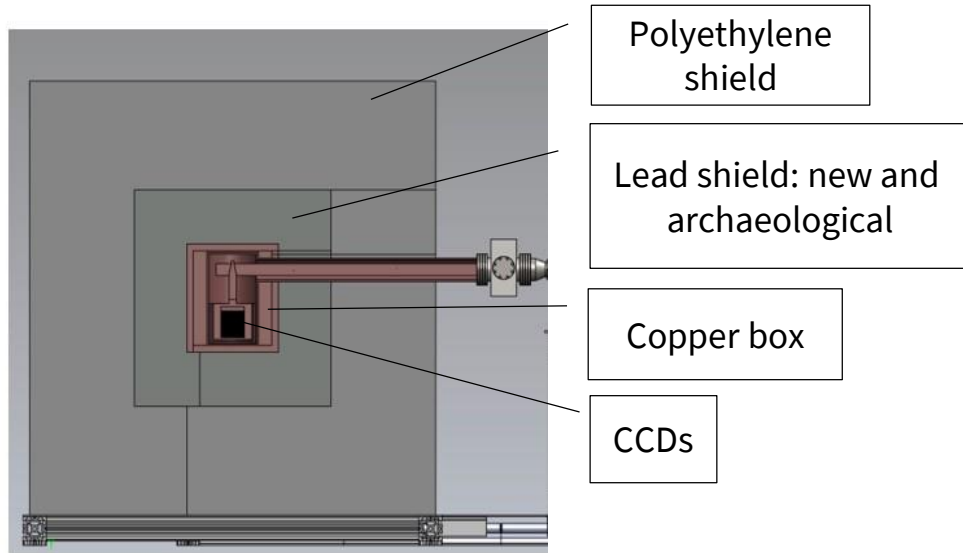


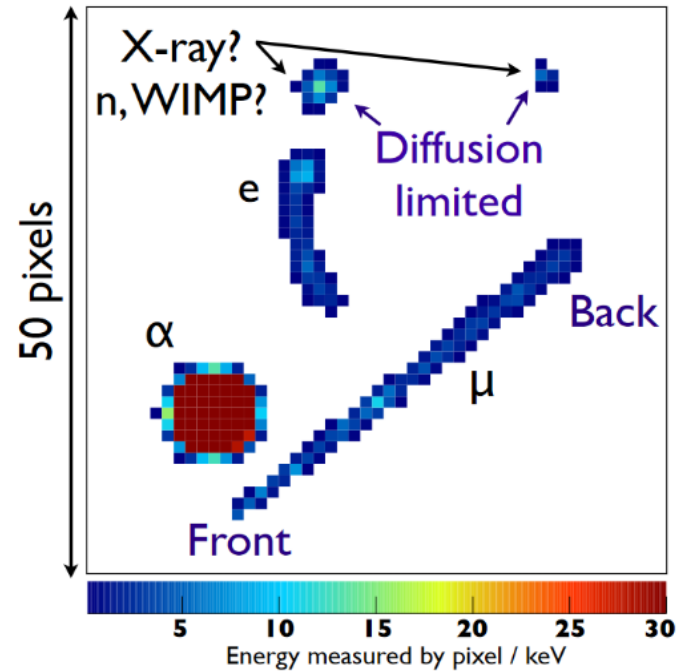
Radon deposition : Limits of GEANT4

Ali Dastgheibi Fard
Guillaume Warot

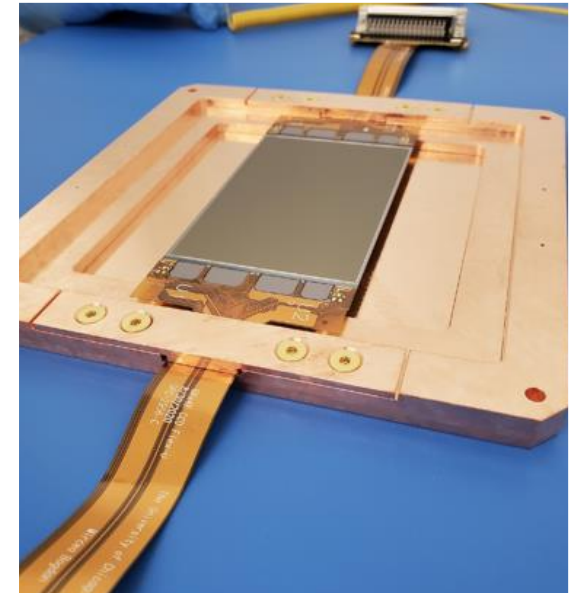
DAMIC-M experiment



Side-view of the DAMIC-M experiment
<https://damic.uchicago.edu/detector.php>



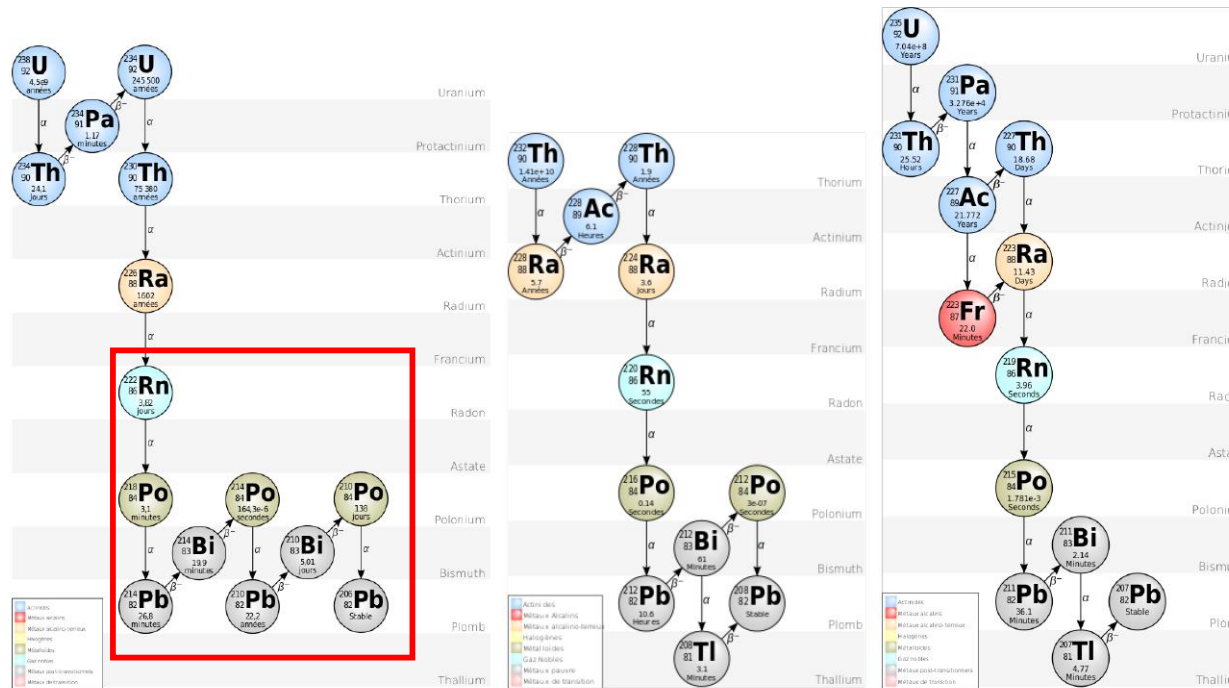
A 50x50 pixel portion of a CCD image that shows tracks of different particles
<https://damic.uchicago.edu/detector.php>



CCD in its support frame

DAMIC-M Radioactive Background

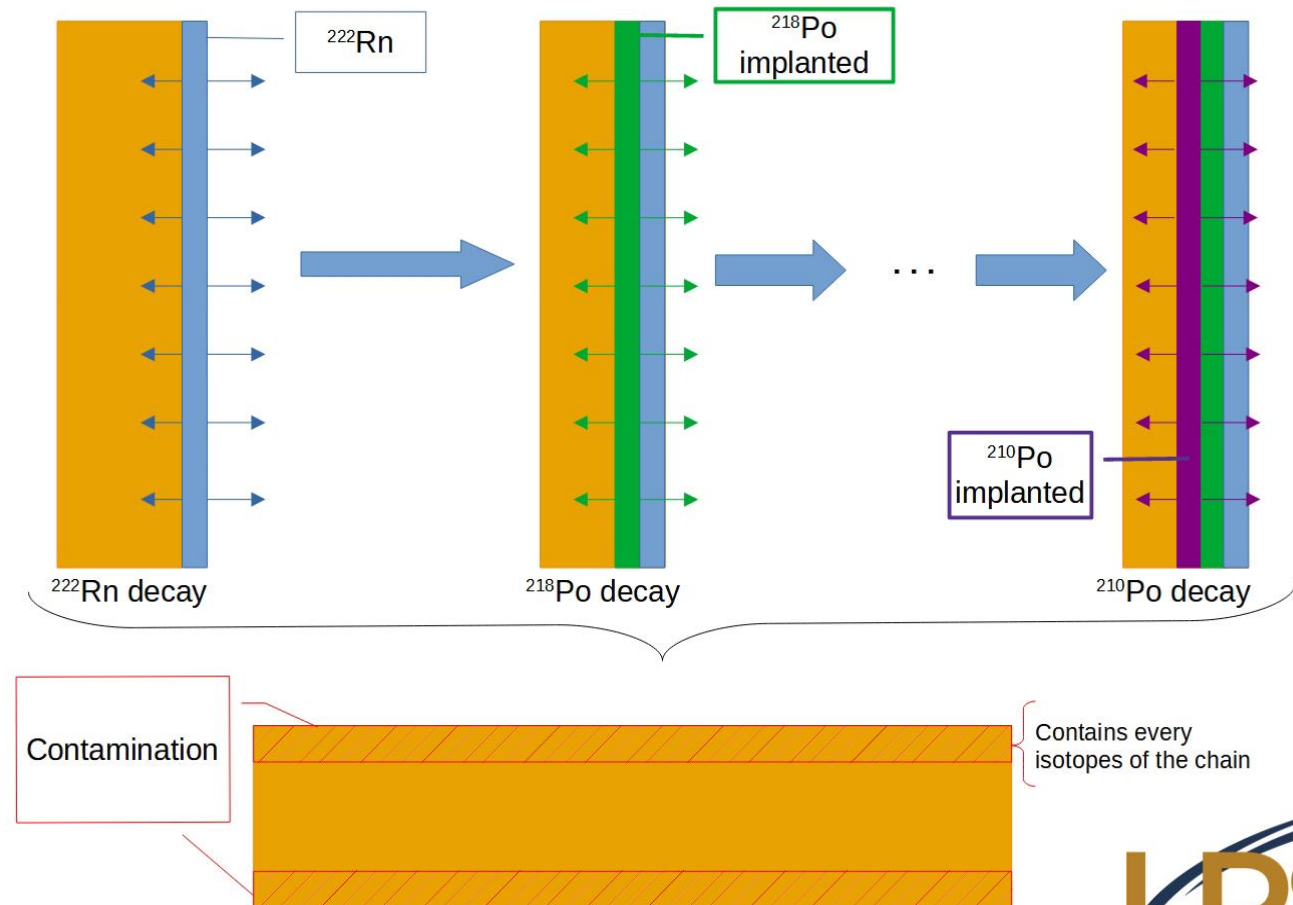
- Cosmogenic contamination
- Internal contamination



Airborne contamination due to radon daughter

Theory

- First deposition of radon or radon daughter is triggered by chemical properties
- Study of implantation using Geant4 to probe nuclear recoil
- Studied in the frame of DAMIC-M radon deposition
- Intern Theo Dubroca



Radon implantation model

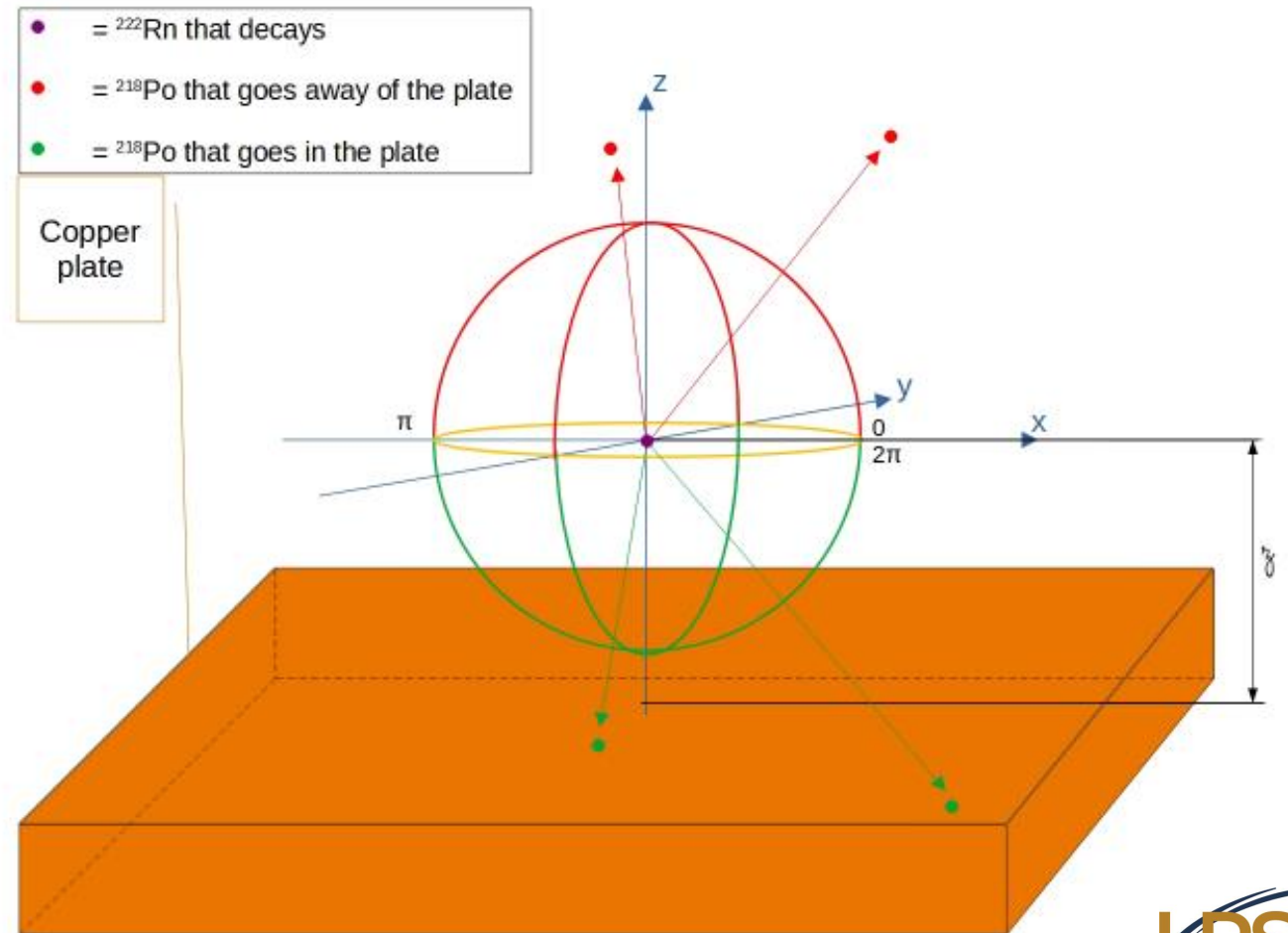
Modelisation Radon daughters:

- On the surface
- In the bulk (z tbd)
- Define a function for each isotope according the obtained curve

An internal new contamination

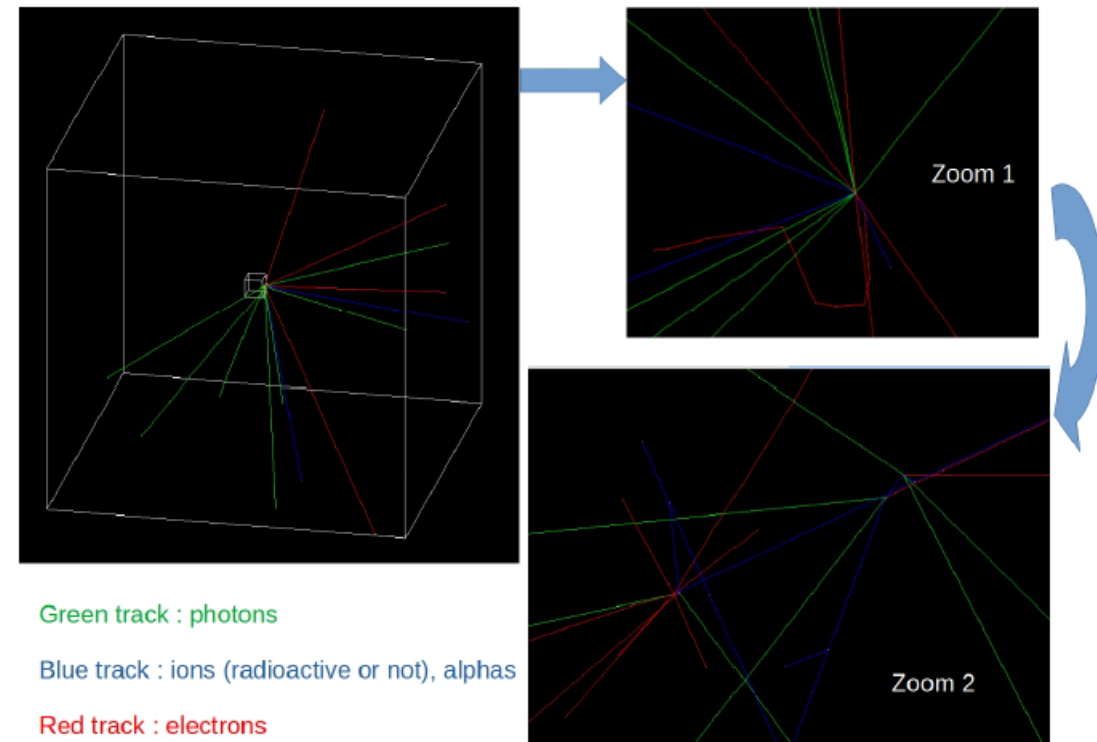
Which impact for detector ?

These information will be an input for DAMICM background simulation



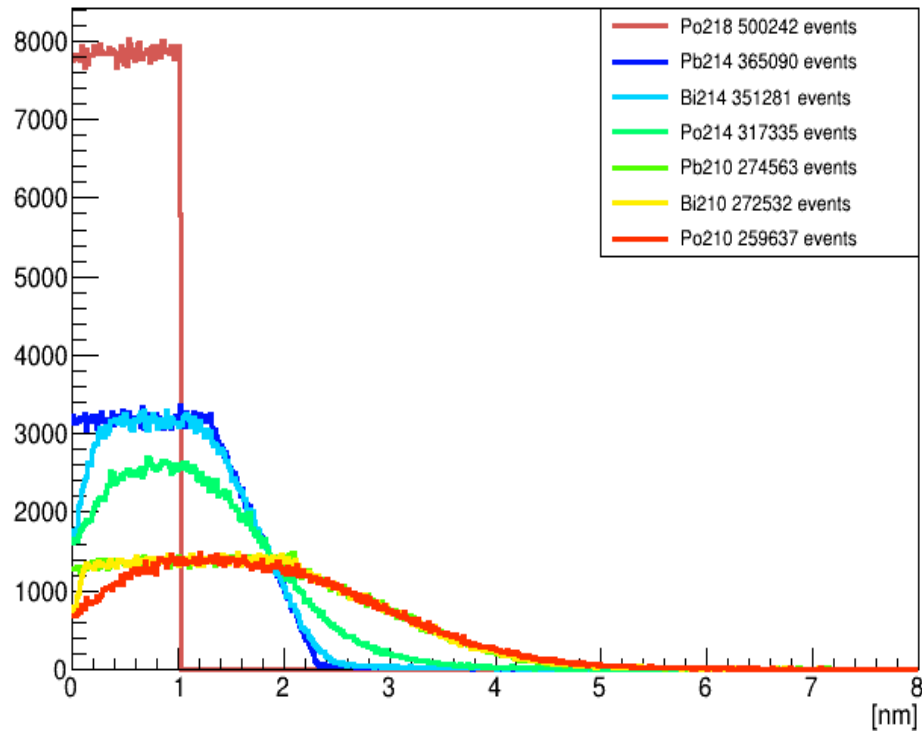
Simulation

- Geometry
- Deposition of an ion on the surface of material
- Position (0,0,0) on the surface and material below
- Full decay
- Record of the position of each nucleus daughter
- Plot projection on z axis
- Code Given by A Brossard on behalf of News-g collaboration

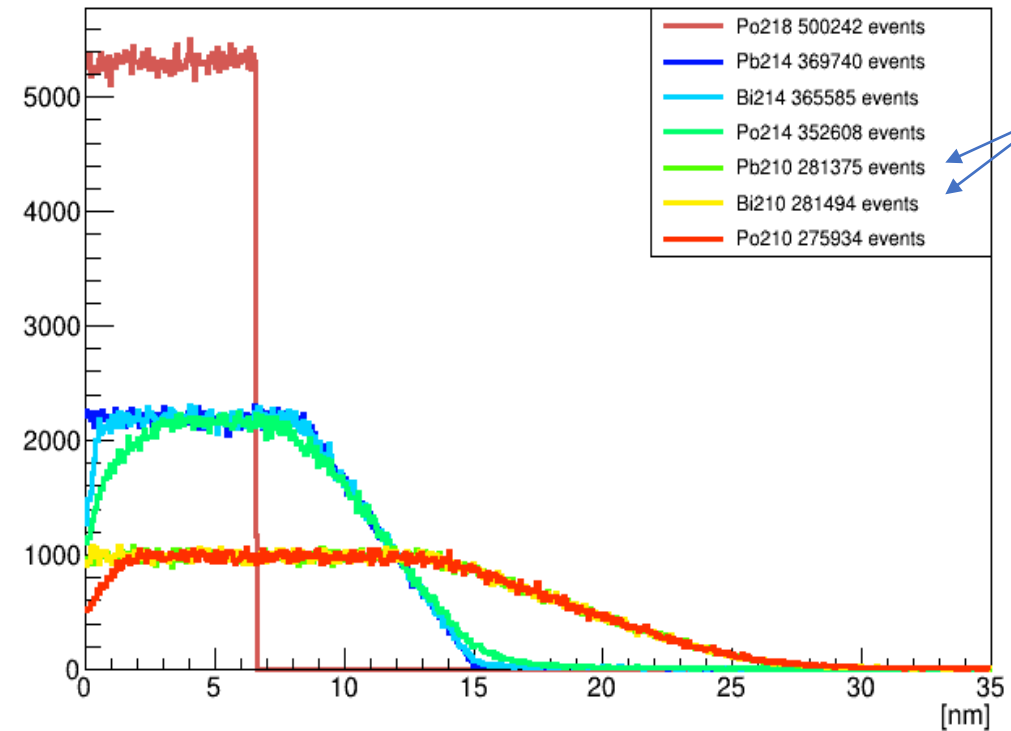


First results source on the surface

Position of decays following 10^6 decays of ^{222}Rn on surface of Cu



Position of decays following 10^6 decays of ^{222}Rn on surface of Si



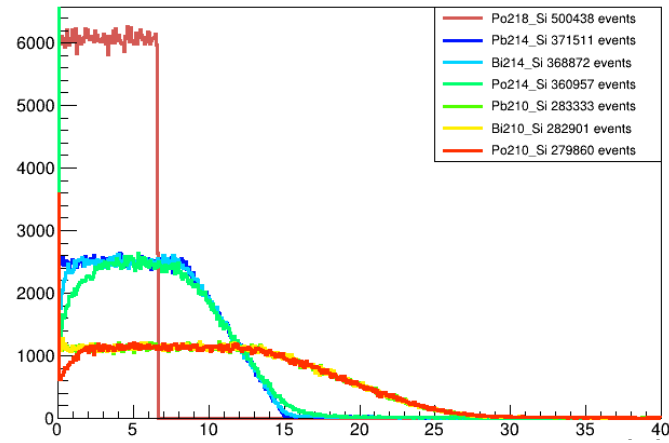
Augmentation of number of event theoretically impossible

Recoil penetration is Z and density dependent

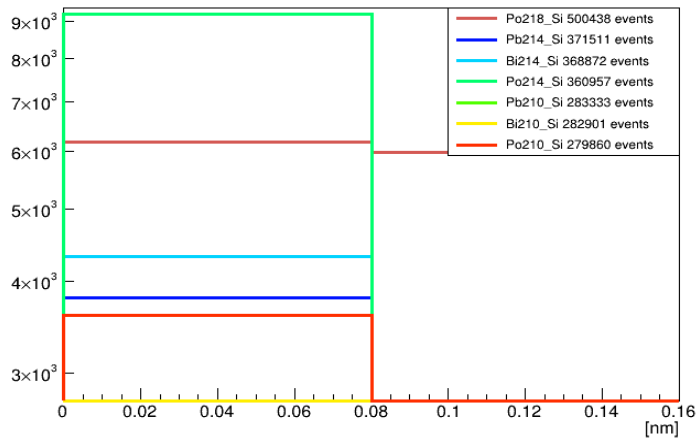
Depth improbably low

Histograms of the implantation depth are drawn without the condition :
 “if z > 1E-6 ” allowing to see unexpected surface event.

Position of decays following 1E6 decays of ^{222}Rn at the surface of Si



Position of decays following 1E6 decays of ^{222}Rn at the surface of Si

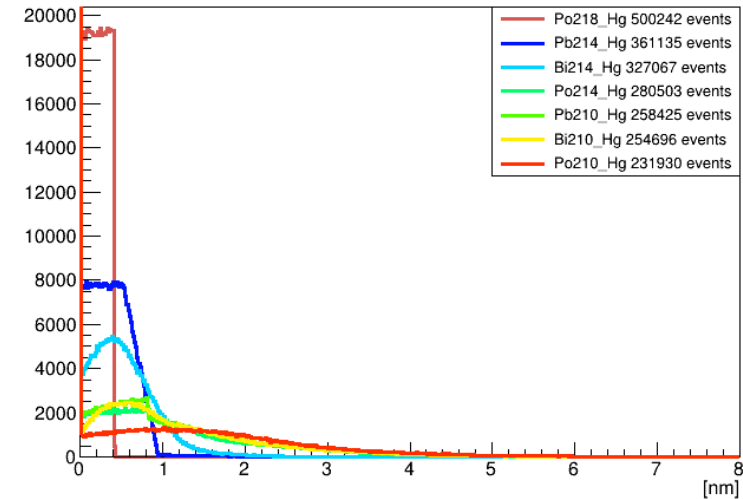


Phenomenon enhanced by using high Z material

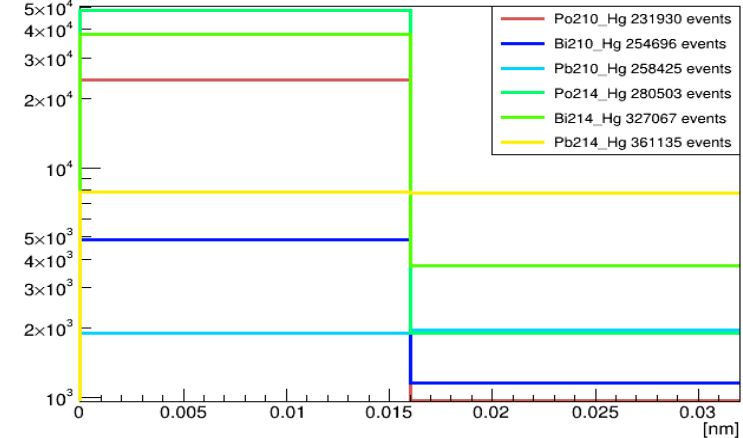
First position of nuclei are improbable , below 0,1 nm meaning less than 1 atom

```
{
  if (Z > 1.e-6) h_Amplitude->Fill(Z/10.);
}
```

Position of decays following 1E6 decays of ^{222}Rn at the surface of Hg

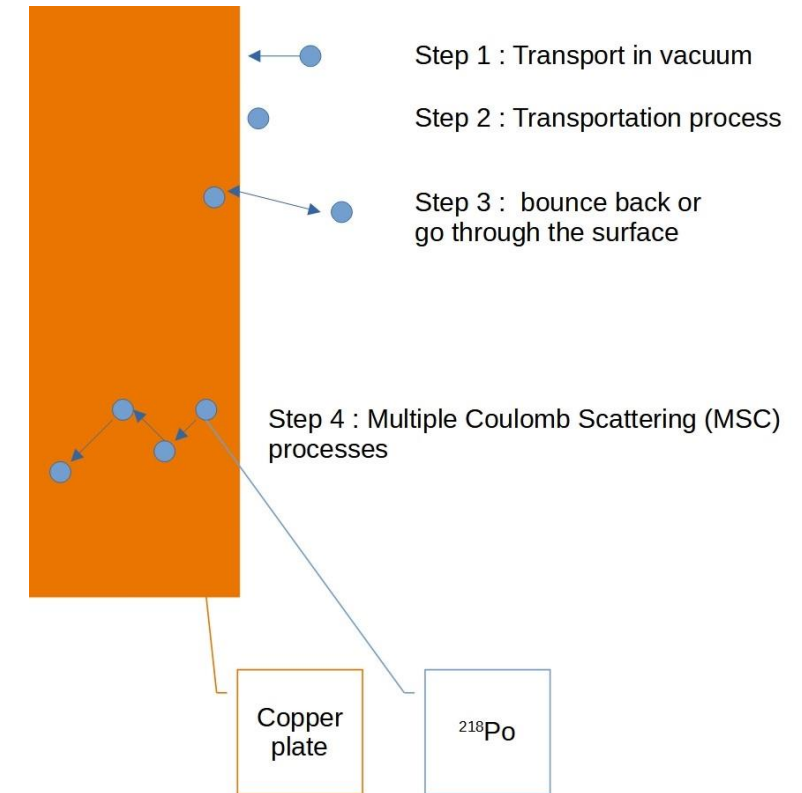
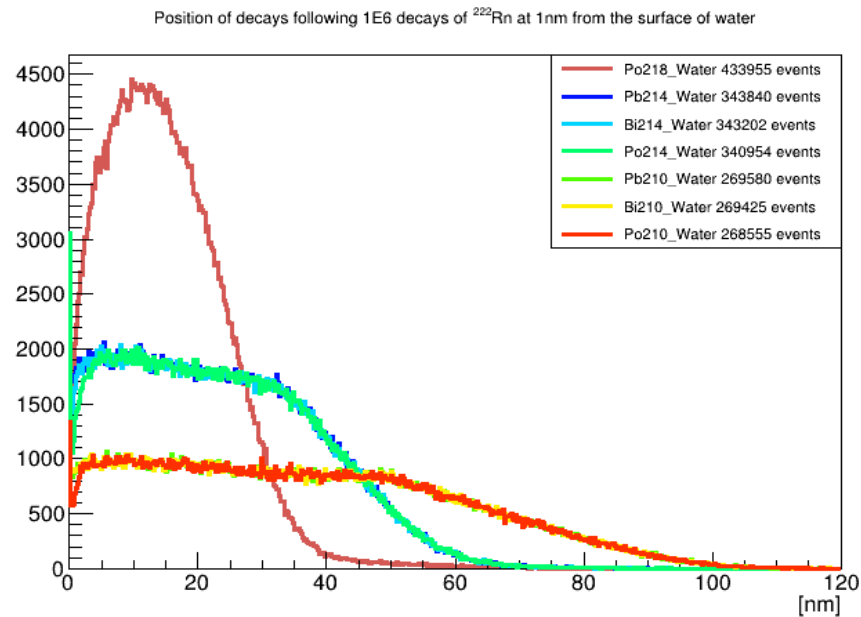


Position of decays following 1E6 decays of ^{222}Rn at the surface of Hg



Interaction with surface

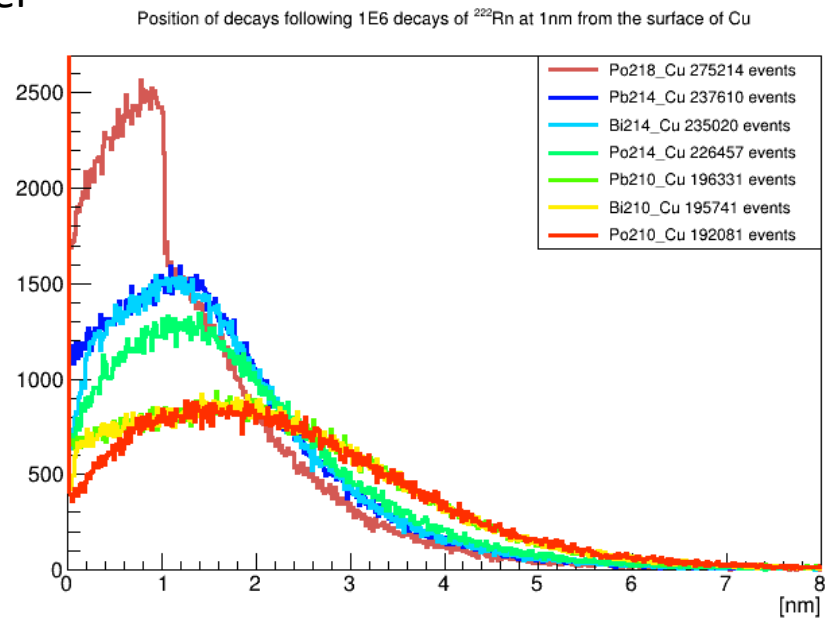
- Changing decay position to (0,0,1) nm
- New shape of the curve



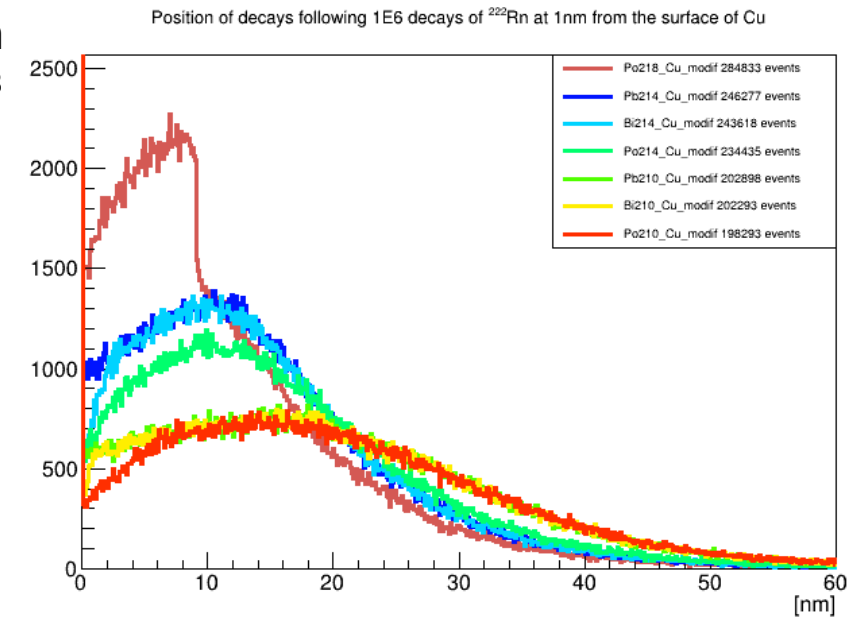
Imperfection in the shape

- Discontinuity for higher Z
- Independant from density

Copper

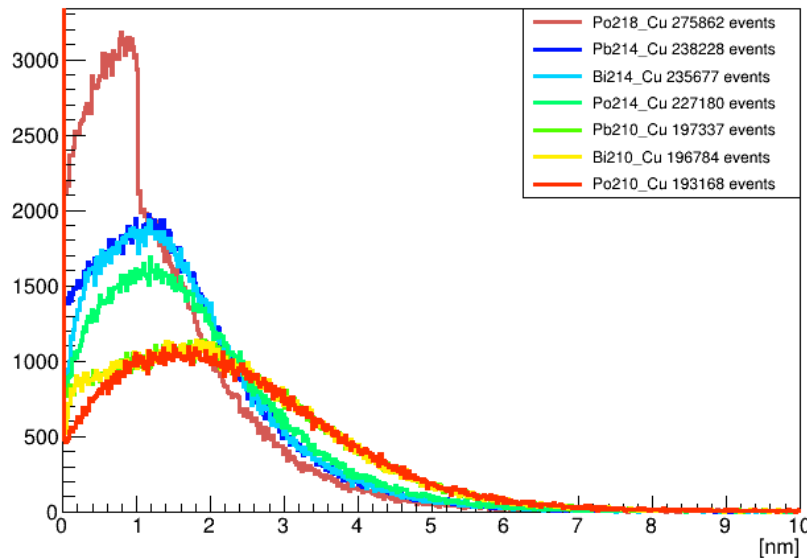


*Copper with $\rho = 1.0 \text{ g.cm}^{-3}$



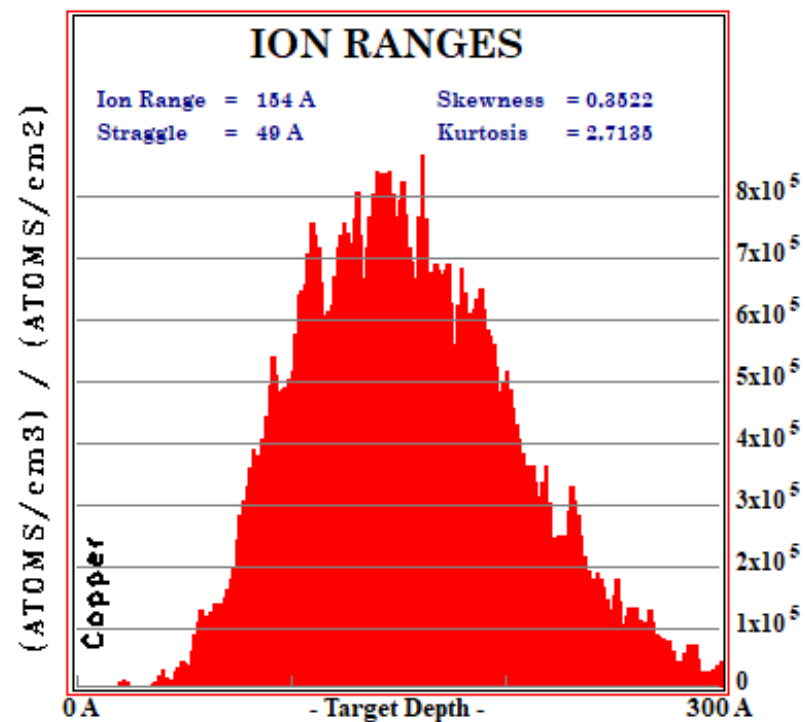
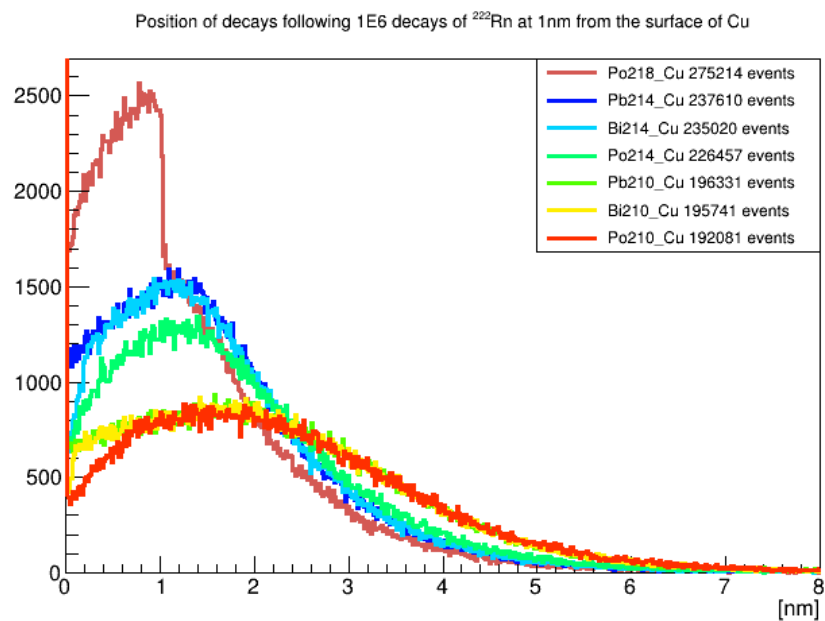
Forcing G4step

- Using a step max (any) will reproduce (0,0,z) decay point
- Console shows that Compton scattering process is used instead of MSC process producing smoother but not continuous curves



G4stepmax
forced to 1 μ m

Comparison GEANT4 vs Srim

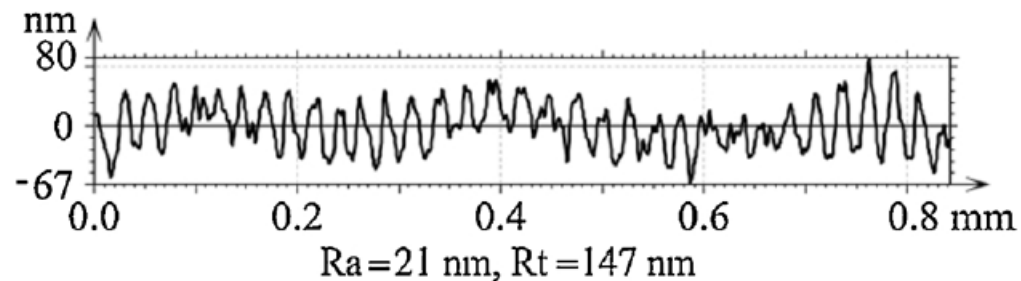


^{218}Po depth range in copper – SRIM 2013

Simulation and reality

- Simulation uses a infinitely flat surface
- Real copper side view for example (optimised OFHC)

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- Reproducing these shape in GEANT 4

Conclusion

- Dependences from starting decay point on results of ion implantation
- Propagation through surface turns on complex simulation mechanism
- Decay can also be properly tracked by set a UserStepMax
- Questions arose about the surface roughness of material compared to penetration of ions
- How to calibrate the results at low energy
- Thanks to Mariangela for the support